

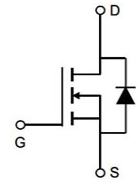
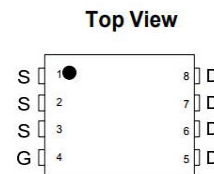
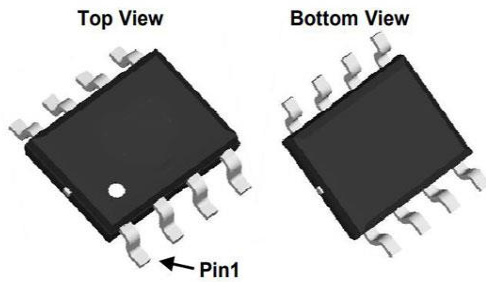
**General Description**

30V /6A Complementary NP Power MOSFET

 Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=4.5\text{ V}$ 

Pb-free lead plating; RoHS compliant

$V_{DS}$	30	V
$R_{DS(on),TYP@VGS=10V}$	29.4	m $\Omega$
$R_{DS(on),TYP@VGS=4.5}$	46.2	m $\Omega$
$I_D$	6	A



Part ID	Package Type	Marking	Tape and reel information
AC4606	SOP8	4606	3000


 100% UIS Tested  
 100% kg Tested

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	20	$\pm V$
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	9.6	
Avalanche Current <sup>G</sup>	$I_{AR}$	1.9	
Repetitive avalanche energy $L=0.1\text{mH}$ <sup>G</sup>	$E_{AR}$	4.4	mJ
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	105	157	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient <sup>A</sup>		Steady State	210	252
Maximum Junction-to-Lead <sup>c</sup>	$R_{\theta JL}$	63	100	$^\circ\text{C}/\text{W}$

**STATIC PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> = -250uA, V <sub>GS</sub> = 0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	uA
					5	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250μA	1.2	1.8	2.4	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =6A		29.4	42.0	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A		46.2	60.1	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =6A		83		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =18V		0.72	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				6	A

**DYNAMIC PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		255	311	pF
C <sub>oss</sub>	Output Capacitance			45	55	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			35	41	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz			0.65	Ω

**SWITCHING PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =6A		2.55		nC
Q <sub>g</sub> 4.5V)	Total Gate Charge			1.275		
Q <sub>gs</sub>	Gate Source Charge			0.91		
Q <sub>gd</sub>	Gate Drain Charge			1.3		
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		4.25		ns
t <sub>r</sub>	Turn-On Rise Time			3.4		
t <sub>D(off)</sub>	Turn-Off DelayTime			11.9		
t <sub>f</sub>	Turn-Off Fall Time			3.825		
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-8A, dI/dt=500A/μs		8.5		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =18A, dI/dt=500A/μs		2.2		nC

